10V Drive Nch MOSFET RK3055E

Structure

Silicon N-channel MOSFET

Features

- 1) Low On-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) 10V drive.
- 5) Drive circuits can be simple.
- 6) Parallel use is easy.

Applications

Switching

Packaging specifications

Туре	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	2500
RK3055E		0

•Dimensions (Unit : mm)



Inner circuit



•Absolute maximum ratings (Ta=25°C)

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Parameter		Symbol	Limits	Unit			
Drain-source voltage		Vdss	60	V			
Gate-source voltage		Vgss	±20	V			
Drain ourrant	Continuous	lo	8	А			
Drain current	Pulsed	Idp*	20	А			
Reverse drain	Continuous	Idr	8	А			
current	Pulsed	Idrp*	20	А			
Total power dissipation (Tc=25°C)		Po	20	W			
Channel temperature		Tch	150	°C			
Storage temperature	e	Tstg	-55 to +150	°C			

* Pw≤10µs, Duty cycle≤1%

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Transistors

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Gate-source leakage	lgss	-	-	±100	nA	Vgs=±20V, Vds=0V
Drain-source breakdown voltage	V(BR)DSS	60	_	-	V	ID=1mA, VGs=0V
Zero gate voltage drain current	IDSS	_	_	10	μΑ	VDS=60V, VGS=0V
Gate threshold voltage	VGS(th)	1.0	_	2.5	V	Vos=10V, Io=1mA
Static drain-source on-state resistance	RDS(on)	-	-	0.15	Ω	ID=4A, VGs=10V
Forward transfer admittance	Y _{fs} *	4.0	_	-	S	ID=4A, VDS=15V
Input capacitance	Ciss	-	520	-	pF	VDS=10V
Output capacitance	Coss	-	240	-	pF	Vg=0V
Reverse transfer capacitance	Crss	_	100	-	pF	f=1MHz
Turn-on delay time	td(on)	-	5.0	-	ns	I⊳=2.5A, Voo≒30V
Rise time	tr	_	20	-	ns	Vgs=10V
Turn-off delay time	td(off)	-	50	-	ns	Rι=12Ω
Fall time	tr	_	20	-	ns	Rg=10Ω

* Pw $\leq 300 \mu s, \, Duty \, cycle \leq 1\%$





Fig.1 Maximum Safe Operating Area



Fig.2 Typical Output Characteristics



Fig.3 Typical Transfer Characteristics



Fig.4 Gate Threshold Voltage Fig. vs. Channel Temperature



10

V_{GS}=10V

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (I)



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V_{GS}=4V



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Fig.7 Static Drain-Source On-State Resistance

vs. Gate-Source Voltage



Fig.8 Static Drain-Source On-State Resistance vs. Channel Temperature



Fig.9 Forward Transfer Admittance vs. Drain Current







Fig.11 Reverse Drain Current

vs. Source-Drain Voltage (II)



Fig.12 Typical Capacitance vs. Drain-Source Voltage







Fig.14 Reverse Recovery Time vs. Reverse Drain Current

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Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

•Switching characteristics measurement circuit





Fig.16 Switching Time Test Circuit

Fig.17 Switching Time Waveforms

Notes

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